

Taichi Otsuji

List of Publications by Year in descending order

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434
papers

8,683
citations

50276

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74163

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437
all docs

437
docs citations

437
times ranked

3735
citing authors

#	ARTICLE	IF	CITATIONS
1	Terahertz-wave generation using graphene: Toward new types of terahertz lasers. Proceedings of the IEEE, 2024, , 1-13.	21.3	1
2	Enhanced terahertz detection of multigate graphene nanostructures. Nanophotonics, 2022, 11, 519-529.	6.0	17
3	Graphene-based plasmonic metamaterial for terahertz laser transistors. Nanophotonics, 2022, 11, 1677-1696.	6.0	15
4	Graphene-based plasma-wave devices for terahertz applications. , 2022, , .		0
5	Boosting photoconductive large-area THz emitter via optical light confinement behind a highly refractive sapphire-fiber lens. Optics Letters, 2022, 47, 1899.	3.3	9
6	Coulomb drag and plasmonic effects in graphene field-effect transistors enable resonant terahertz detection. Applied Physics Letters, 2022, 120, 111102.	3.3	3
7	Optical up-conversion-based cross-correlation for characterization of sub-nanosecond terahertz-wave pulses. Optics Express, 2022, 30, 11217.	3.4	7
8	Plasma-Wave Devices. Springer Series in Optical Sciences, 2022, , 291-296.	0.7	0
9	Bias voltage dependency of plasmonic instability and terahertz radiation in a dual-grating-gate high-electron-mobility transistor. , 2021, , .		0
10	Terahertz emission in an InGaAs-based dual-grating-gate high-electron-mobility transistor plasmonic photomixer. Applied Physics Express, 2021, 14, 051001.	2.4	3
11	Unitraveling-Carrier-Photodiode-Integrated High-Electron-Mobility Transistor for Photonic Double-Mixing. Journal of Lightwave Technology, 2021, 39, 3341-3349.	4.6	8
12	Optical-to-Wireless Carrier Frequency Down-Conversion by UTC-PD-Integrated HEMT: Dependence of Conversion Gain on UTC-PD Mesa Size. , 2021, , .		1
13	Modulation characteristics of uncooled graphene photodetectors. Journal of Applied Physics, 2021, 129, .	2.5	10
14	Fast terahertz detection by asymmetric dual-grating-gate graphene FET. , 2021, , .		1
15	Heat capacity of nonequilibrium electron-hole plasma in graphene layers and graphene bilayers. Physical Review B, 2021, 103, .	3.2	2
16	1-THz plasmonic double-mixing in a dual-grating-gate high-electron- mobility transistor. , 2021, , . S-Shaped Current-Voltage Characteristics of		0
17	$\frac{dI}{dV} = \frac{dI}{dV} + \frac{dI}{dV} - \frac{dI}{dV}$	3.8	18
18	Coulomb electron drag mechanism of terahertz plasma instability in n+-i-n-n+ graphene FETs with ballistic injection. Applied Physics Letters, 2021, 119, .	3.3	13

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37	Far-infrared and terahertz emitting diodes based on graphene/black-P and graphene/MoS2 heterostructures. Optics Express, 2020, 28, 24136.	3.4	7
38	Frequency-agile injection-seeded terahertz-wave parametric generation: publisher's note. Optics Letters, 2020, 45, 627.	3.3	1
39	Frequency-agile injection-seeded terahertz-wave parametric generation. Optics Letters, 2020, 45, 77.	3.3	6
40	Nanoscale probing of thermally excited evanescent fields in an electrically biased graphene by near-field optical microscopy. Applied Physics Express, 2020, 13, 096501.	2.4	9
41	Far-infrared photodetection in graphene nanoribbon heterostructures with black-phosphorus base layers. Optical Engineering, 2020, 60, .	1.0	1
42	Gate-Readout of Photovoltage from a Grating-Gate Plasmonic THz Detector. , 2020, , .		6
43	Investigation of Terahertz properties in Graphene ribbons. , 2020, , .		3
44	Terahertz Emission in an Asymmetric Dual-Grating-Gate High-Electron Mobility Transistor Plasmonic Photomixer under dc Current Flow. , 2020, , .		0
45	Room Temperature Amplification of Terahertz Radiation by Grating-Gate Monolayer Graphene-Channel Transistor Structures. , 2020, , .		1
46	Concepts of infrared and terahertz photodetectors based on vertical graphene van der Waals and HgTe-CdHgTe heterostructures. Opto-electronics Review, 2019, 27, 219-223.	2.4	2
47	Optical-to-THz Frequency Down-Conversion Utilizing Two-Dimensional Plasmons. , 2019, , .		1
48	Negative terahertz conductivity and amplification of surface plasmons in graphene's black phosphorus injection laser heterostructures. Physical Review B, 2019, 100, .	3.2	21
49	Characteristics of vertically stacked graphene-layer infrared photodetectors. Solid-State Electronics, 2019, 155, 123-128.	1.4	1
50	Negative photoconductivity and hot-carrier bolometric detection of terahertz radiation in graphene-phosphorene hybrid structures. Journal of Applied Physics, 2019, 125, 151608.	2.5	12
51	Optical Pumping of Graphene-Based Heterostructures with Black-Arsenic-Phosphorus Absorbing-Cooling Layer for Terahertz Lasing. , 2019, , .		0
52	Asymmetric Dual Grating Gate Graphene-based THz detectors. , 2019, , .		0
53	Terahertz Emission from an Asymmetric Dual-Grating-Gate InGaAs High-Electron-Mobility Transistor Stimulated by Plasmonic Boom Instability. , 2019, , .		1
54	Negative Terahertz Conductivity at Vertical Carrier Injection in a Black-Arsenic-Phosphorus's Graphene Heterostructure Integrated With a Light-Emitting Diode. IEEE Journal of Selected Topics in Quantum Electronics, 2019, 25, 1-9.	2.9	4

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55	Terahertz plasmon-emitting graphene-channel transistor. <i>Opto-electronics Review</i> , 2019, 27, 345-347.	2.4	6
56	Terahertz photoconductive emitter with dielectric-embedded high-aspect-ratio plasmonic grating for operation with low-power optical pumps. <i>AIP Advances</i> , 2019, 9, .	1.3	43
57	Optical pumping in graphene-based terahertz/far-infrared superluminescent and laser heterostructures with graded-gap black-PxAs _{1-x} absorbing-cooling layers. <i>Optical Engineering</i> , 2019, 59, 1.	1.0	8
58	Metallic and dielectric metasurfaces in photoconductive terahertz devices: a review. <i>Optical Engineering</i> , 2019, 59, 1.	1.0	61
59	Graphene-based van der Waals heterostructures towards a new type of terahertz quantum-cascade lasers. , 2019, , .		1
60	Negative and positive terahertz and infrared photoconductivity in uncooled graphene. <i>Optical Materials Express</i> , 2019, 9, 585.	3.0	24
61	Optical pumping through a black-As absorbing-cooling layer in graphene-based heterostructure: thermo-diffusion model. <i>Optical Materials Express</i> , 2019, 9, 4061.	3.0	9
62	UTC-PD-Integrated HEMT for Optical-to-Millimeter-Wave Carrier Frequency Down-Conversion. , 2019, , .		2
63	Graphene-based 2D-heterostructures for terahertz lasers and amplifiers. , 2019, , .		1
64	Plasmonic terahertz emitters with high-aspect ratio metal gratings. , 2019, , .		0
65	Terahertz light amplification of stimulated emission of radiation in current-injection graphene channel transistor. , 2019, , .		0
66	Vertical Hot-electron Terahertz Detectors Based on Black-As _{1-x} Px/graphene/black-As _{1-y} Py Heterostructures. <i>Sensors and Materials</i> , 2019, 31, 2271.	0.5	2
67	Lateral terahertz hot-electron bolometer based on an array of Sn nanothreads in GaAs. <i>Journal Physics D: Applied Physics</i> , 2018, 51, 135101.	2.8	17
68	Comparison of Intersubband Quantum-Well and Interband Graphene-Layer Infrared Photodetectors. <i>IEEE Journal of Quantum Electronics</i> , 2018, 54, 1-8.	1.9	9
69	Device model for pixelless infrared image up-converters based on polycrystalline graphene heterostructures. <i>Journal of Applied Physics</i> , 2018, 123, 014503.	2.5	3
70	Terahertz light-emitting graphene-channel transistor toward single-mode lasing. <i>Nanophotonics</i> , 2018, 7, 741-752.	6.0	57
71	Manifestation of plasmonic response in the detection of sub-terahertz radiation by graphene-based devices. <i>Nanotechnology</i> , 2018, 29, 245204.	2.6	18
72	Plasmonic terahertz antennas with high-aspect ratio metal gratings. <i>EPJ Web of Conferences</i> , 2018, 195, 02009.	0.3	2

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73	Coupling of 2D Plasmons in Grating-Gate Plasmonic THz Detector to THz Wave with Lateral Polarization. , 2018, , .		3
74	Sn-nanowires in GaAs matrix and their sub- and terahertz applications. Journal of Physics: Conference Series, 2018, 1092, 012166.	0.4	5
75	Electrical modulation of terahertz radiation using graphene-phosphorene heterostructures. Semiconductor Science and Technology, 2018, 33, 124010.	2.0	19
76	Real-space-transfer mechanism of negative differential conductivity in gated graphene-phosphorene hybrid structures: Phenomenological heating model. Journal of Applied Physics, 2018, 124, 114501.	2.5	15
77	Interband infrared photodetectors based on HgTe/CdHgTe quantum-well heterostructures. Optical Materials Express, 2018, 8, 1349.	3.0	13
78	Infrared photodetectors based on graphene van der Waals heterostructures. Infrared Physics and Technology, 2017, 84, 72-81.	2.9	17
79	Dynamic Conductivity and Two-Dimensional Plasmons in Lateral CNT Networks. International Journal of High Speed Electronics and Systems, 2017, 26, 1740004.	0.7	0
80	Current-injection terahertz lasing in a distributed-feedback dual-gate graphene-channel transistor. Proceedings of SPIE, 2017, , .	0.8	0
81	Plasmonic amplification of terahertz radiation in a periodic graphene structure with the carrier injection. Applied Physics Letters, 2017, 111, .	3.3	27
82	Infrared detection and photon energy up-conversion in graphene layer infrared photodetectors integrated with LEDs based on van der Waals heterostructures: Concept, device model, and characteristics. Infrared Physics and Technology, 2017, 85, 307-314.	2.9	3
83	Neutral beam process in AlGaIn/GaN HEMTs: Impact on current collapse. Solid-State Electronics, 2017, 137, 1-5.	1.4	9
84	Effect of doping on the characteristics of infrared photodetectors based on van der Waals heterostructures with multiple graphene layers. Journal of Applied Physics, 2017, 122, .	2.5	12
85	Neutral beam etching for device isolation in AlGaIn/GaN HEMTs. Physica Status Solidi (A) Applications and Materials Science, 2017, 214, 1600617.	1.8	5
86	Detection and up-conversion of infrared radiation using van der Waals heterostructures with graphene layers. , 2017, , .		0
87	Lens-integrated asymmetric-dual-grating-gate high-electron-mobility-transistor for plasmonic terahertz detection. , 2017, , .		2
88	High-speed pulse response of asymmetric-dual-grating-gate high-electron-mobility-transistor for plasmonic THz detection. , 2017, , .		1
89	Solution-based formation of high-quality gate dielectrics on epitaxial graphene by microwave-assisted annealing. Japanese Journal of Applied Physics, 2017, 56, 06GF09.	1.5	2
90	Nonlinear response of infrared photodetectors based on van der Waals heterostructures with graphene layers. Optics Express, 2017, 25, 5536.	3.4	18

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91	Broadband Terahertz-Light Emission by Current-Injection Distributed-Feedback Dual-Gate Graphene-Channel Field-Effect Transistor. , 2017, , .		1
92	Physics of Terahertz-Wave Generation Using Plasmon Resonance and its Application to the Light-Source Devices. The Review of Laser Engineering, 2017, 45, 746.	0.0	0
93	Millimeter-wave/terahertz detection and photonic double-mixing by transistors. , 2017, , .		4
94	Terahertz Optoelectronics in Graphene. Hyomen Kagaku, 2016, 37, 553-559.	0.0	0
95	Ultra-compact injection terahertz laser using the resonant inter-layer radiative transitions in multi-graphene-layer structure. Optics Express, 2016, 24, 29603.	3.4	11
96	5.2-THz single-mode lasing in current-injection distributed-feedback dual-gate graphene-channel field-effect transistor. , 2016, , .		0
97	Design and Fabrication of Terahertz Detectors Based on 180-nm CMOS Process Technology. International Journal of High Speed Electronics and Systems, 2016, 25, 1640014.	0.7	1
98	Plasmonic Enhancement of Terahertz Devices Efficiency. International Journal of High Speed Electronics and Systems, 2016, 25, 1640019.	0.7	0
99	Achievement of balanced high frequency and high breakdown by InGaAs-based high-electron-mobility transistors with slant field plates. Applied Physics Express, 2016, 9, 114101.	2.4	2
100	Resonant plasmonic terahertz detection in graphene split-gate field-effect transistors with lateral p-n junctions. Journal Physics D: Applied Physics, 2016, 49, 315103.	2.8	27
101	Solution-processed Al ₂ O ₃ gate dielectrics for graphene field-effect transistors. Japanese Journal of Applied Physics, 2016, 55, 091502.	1.5	6
102	Two-dimensional plasmons in lateral carbon nanotube network structures and their effect on the terahertz radiation detection. Journal of Applied Physics, 2016, 120, 044501.	2.5	18
103	Nanostructured asymmetric dual-grating-gate plasmonic THz detectors: Enhancement of external coupling efficiency by array configuration and silicon-lens integration. , 2016, , .		1
104	High-performance self-aligned graphene transistors fabricated using contamination- and defect-free process. Japanese Journal of Applied Physics, 2016, 55, 06GF11.	1.5	1
105	Array configuration and silicon-lens integration of asymmetric dual-grating-gate plasmonic THz detectors. , 2016, , .		4
106	Enhanced Terahertz Emission from Monolayer Graphene with Metal Mesh Structure. Materials Today: Proceedings, 2016, 3, S221-S226.	1.8	0
107	Graphene-based van der Waals heterostructures for emission and detection of terahertz radiation. Proceedings of SPIE, 2016, , .	0.8	2
108	Cooperative promotion of plasma instabilities for emission of terahertz radiation in an asymmetric dual-grating-gate graphene-channel FET. , 2016, , .		2

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109	Plasmons in tunnel-coupled graphene layers: Backward waves with quantum cascade gain. Physical Review B, 2016, 94, .	3.2	32
110	A Fitting Model for Asymmetric ϵ'' Characteristics of Graphene FETs for Extraction of Intrinsic Mobilities. IEEE Transactions on Electron Devices, 2016, 63, 3300-3306.	3.0	11
111	Giant plasmon instability in a dual-grating-gate graphene field-effect transistor. Physical Review B, 2016, 93, .	3.2	42
112	Models for plasmonic THz detectors based on graphene split-gate FETs with lateral p-n junctions. , 2016, , .		0
113	Terahertz wave generation and detection in double-graphene layered van der Waals heterostructures. 2D Materials, 2016, 3, 045009.	4.4	56
114	A new process approach for slant field plates in GaN-based high-electron-mobility transistors. Japanese Journal of Applied Physics, 2016, 55, 01AD02.	1.5	11
115	Photonic Frequency Double-Mixing Conversion Over the 120-GHz Band Using InP- and Graphene-Based Transistors. Journal of Lightwave Technology, 2016, 34, 2011-2019.	4.6	14
116	Sub-THz photonic frequency conversion using optoelectronic transistors for future fully coherent access network systems. , 2016, , .		0
117	Current-Injection Terahertz Lasing in Distributed-Feedback Dual-Gate Graphene-Channel Field-Effect Transistor. , 2016, , .		0
118	Sub-THz photonic frequency conversion using graphene and InP-based transistors for future fully coherent access network. , 2015, , .		0
119	Resonant plasmonic terahertz detection in vertical graphene-base hot-electron transistors. Journal of Applied Physics, 2015, 118, .	2.5	16
120	Negative terahertz conductivity in remotely doped graphene bilayer heterostructures. Journal of Applied Physics, 2015, 118, .	2.5	4
121	Effects of carrier-carrier scattering on population inversion in graphene under pulse photoexcitation. Journal of Physics: Conference Series, 2015, 584, 012018.	0.4	6
122	Graphene active plasmonics for terahertz device applications. , 2015, , .		0
123	Photonic frequency conversion using graphene FETs for future fully coherent access network. , 2015, , .		0
124	Vertical hot-electron graphene-base transistors as resonant plasmonic terahertz detectors. , 2015, , .		0
125	Superradiant amplification of terahertz radiation by plasmons in inverted graphene with a planar distributed Bragg resonator. Semiconductors, 2015, 49, 1468-1472.	0.5	2
126	Broadband characteristics of ultrahigh responsivity of asymmetric dual-grating-gate plasmonic terahertz detectors. , 2015, , .		1

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127	Emission and detection of terahertz radiation in double-graphene-layer van der waals heterostructures. , 2015, , .		0
128	Graphene Active Plasmonics for New Types of Terahertz Lasers. , 2015, , .		1
129	Active guiding of Dirac plasmons in graphene. Applied Physics Letters, 2015, 106, 061105.	3.3	22
130	Controlled oxygen-doped diamond-like carbon film synthesized by photoemission-assisted plasma. Diamond and Related Materials, 2015, 53, 11-17.	3.9	10
131	Graphene vertical cascade interband terahertz and infrared photodetectors. 2D Materials, 2015, 2, 025002.	4.4	20
132	Vertical electron transport in van der Waals heterostructures with graphene layers. Journal of Applied Physics, 2015, 117, 154504.	2.5	11
133	Room-temperature zero-bias plasmonic THz detection by asymmetric dual-grating-gate HEMT. Proceedings of SPIE, 2015, , .	0.8	0
134	Recent advances in the research toward graphene-based terahertz lasers. , 2015, , .		4
135	Helicity sensitive terahertz radiation detection by dual-grating-gate high electron mobility transistors. Journal of Applied Physics, 2015, 118, .	2.5	23
136	InGaAs channel HEMTs for photonic frequency double mixing conversion over the sub-THz band. , 2015, , .		1
137	Terahertz Wave Generation Using Graphene and Compound Semiconductor Nano-Heterostructures. Nanostructure Science and Technology, 2015, , 237-261.	0.1	0
138	Electron Capture in van der Waals Graphene-Based Heterostructures with WS ₂ Barrier Layers. Journal of the Physical Society of Japan, 2015, 84, 094703.	1.6	18
139	Negative terahertz conductivity in disordered graphene bilayers with population inversion. Applied Physics Letters, 2015, 106, 113501.	3.3	16
140	Terahertz Emission in Double-Graphene-Layer Structure. , 2015, , .		0
141	Graphene-channel FETs for photonic frequency double-mixing conversion over the sub-THz band. Solid-State Electronics, 2015, 103, 216-221.	1.4	62
142	Graphene Terahertz Devices. , 2015, , 105-122.		0
143	Application of Graphene to Ultrahigh-Frequency Optoelectronic Devices. Journal of the Vacuum Society of Japan, 2014, 57, 444-450.	0.3	0
144	Amplification of terahertz radiation by plasmonic graphene metasurfaces. , 2014, , .		0

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145	Graphene Active Plasmonics for New Types of Terahertz Lasers. International Journal of High Speed Electronics and Systems, 2014, 23, 1450016.	0.7	1
146	Graphene nanoelectromechanical resonators for the detection of modulated terahertz radiation. Journal Physics D: Applied Physics, 2014, 47, 505105.	2.8	7
147	S3-P4: Impact of drain conductance in InGaAs-HEMTs operated in a class-F amplifier. , 2014, , .		1
148	S7-N2: Terahertz lasing and detection in double-graphene-layer structures. , 2014, , .		0
149	Carrier-carrier scattering and negative dynamic conductivity in pumped graphene. Optics Express, 2014, 22, 19873.	3.4	33
150	Terahertz Plasmonics: Good Results and Great Expectations. IEEE Microwave Magazine, 2014, 15, 43-50.	0.8	96
151	Graphene vertical hot-electron terahertz detectors. Journal of Applied Physics, 2014, 116, 114504.	2.5	18
152	Double injection, resonant-tunneling recombination, and current-voltage characteristics in double-graphene-layer structures. Journal of Applied Physics, 2014, 115, .	2.5	18
153	Negative dynamic Drude conductivity in pumped graphene. Applied Physics Express, 2014, 7, 115101.	2.4	12
154	Gain Enhancement Effect of Surface Plasmon Polaritons on Terahertz Stimulated Emission in Optically Pumped Monolayer Graphene. , 2014, , .		6
155	Double graphene-layer structures for adaptive devices. , 2014, , .		0
156	Giant terahertz gain by excitation of surface plasmon polarities in optically pumped graphene. , 2014, , .		0
157	Graphene plasmonic heterostructures for new types of terahertz lasers. , 2014, , .		0
158	All-graphene field-effect transistor based on lateral tunnelling. Journal Physics D: Applied Physics, 2014, 47, 094002.	2.8	3
159	Voltage-tunable terahertz and infrared photodetectors based on double-graphene-layer structures. Applied Physics Letters, 2014, 104, .	3.3	32
160	Surface-plasmons lasing in double-graphene-layer structures. Journal of Applied Physics, 2014, 115, 044511.	2.5	21
161	Relationship between the structure and electrical characteristics of diamond-like carbon films. Journal of Applied Physics, 2014, 116, .	2.5	23
162	Impact of T-gate stem height on parasitic gate delay time in InGaAs-HEMTs. Solid-State Electronics, 2014, 102, 93-97.	1.4	51

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163	Ultrahigh sensitive sub-terahertz detection by InP-based asymmetric dual-grating-gate high-electron-mobility transistors and their broadband characteristics. Applied Physics Letters, 2014, 104, .	3.3	158
164	Current collapse suppression in AlGaN/GaN HEMTs by means of slant field plates fabricated by multi-layer SiCN. Solid-State Electronics, 2014, 101, 63-69.	1.4	13
165	Active graphene plasmonics for terahertz device applications. Journal Physics D: Applied Physics, 2014, 47, 094006.	2.8	101
166	Transient stimulated emission from multi-split-gated graphene structure. Journal Physics D: Applied Physics, 2014, 47, 055103.	2.8	1
167	Terahertz emission and detection in double-graphene-layer structures. , 2014, , .		1
168	Challenges to create graphene terahertz lasers. Journal of Physics: Conference Series, 2014, 486, 012007.	0.4	1
169	Current-driven detection of terahertz radiation using a dual-grating-gate plasmonic detector. Applied Physics Letters, 2014, 104, .	3.3	43
170	Graphene plasmonic heterostructures for terahertz device applications. , 2014, , .		0
171	Improved breakdown voltage and RF characteristics in AlGaN/GaN high-electron-mobility transistors achieved by slant field plates. Applied Physics Express, 2014, 7, 096501.	2.4	7
172	Damping mechanism of terahertz plasmons in graphene on heavily doped substrate. Journal of Applied Physics, 2014, 115, 104501.	2.5	10
173	Terahertz and infrared surface plasmon-polaritons in double-graphene layer structures. Journal of Physics: Conference Series, 2014, 486, 012023.	0.4	0
174	Plasma resonant terahertz photomixers based on double graphene layer structures. Journal of Physics: Conference Series, 2014, 486, 012032.	0.4	1
175	Recent Results on Broadband Nanotransistor Based THz Detectors. NATO Science for Peace and Security Series B: Physics and Biophysics, 2014, , 189-209.	0.3	5
176	Terahertz Plasma Field Effect Transistors. Springer Series in Optical Sciences, 2014, , 77-100.	0.7	4
177	Threshold of terahertz population inversion and negative dynamic conductivity in graphene under pulse photoexcitation. Journal of Applied Physics, 2013, 113, .	2.5	45
178	Site-Selective Epitaxy of Graphene on Si Wafers. Proceedings of the IEEE, 2013, 101, 1557-1566.	21.3	13
179	InP- and GaAs-Based Plasmonic High-Electron-Mobility Transistors for Room-Temperature Ultrahigh-Sensitive Terahertz Sensing and Imaging. IEEE Sensors Journal, 2013, 13, 89-99.	4.7	69
180	Double injection in graphene p-i-n structures. Journal of Applied Physics, 2013, 113, 244505.	2.5	32

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181	Hydrodynamic electron transport and nonlinear waves in graphene. <i>Physical Review B</i> , 2013, 88, .	3.2	66
182	Dynamic effects in double graphene-layer structures with inter-layer resonant-tunnelling negative conductivity. <i>Journal Physics D: Applied Physics</i> , 2013, 46, 315107.	2.8	46
183	Injection terahertz laser using the resonant inter-layer radiative transitions in double-graphene-layer structure. <i>Applied Physics Letters</i> , 2013, 103, .	3.3	47
184	Graphene active plasmonics and their applications to terahertz lasers and sensors. <i>Proceedings of SPIE</i> , 2013, , .	0.8	2
185	The gain enhancement effect of surface plasmon polaritons on terahertz stimulated emission in optically pumped monolayer graphene. <i>New Journal of Physics</i> , 2013, 15, 075003.	2.9	94
186	Graphene-channel FETs for photonic frequency double-mixing conversion over the sub-THz band. , 2013, , .		2
187	Observation of terahertz resonant absorption in graphene micro-ribbon arrays. , 2013, , .		0
188	Amplification of terahertz radiation by plasmons in graphene with a planar Bragg grating. , 2013, , .		0
189	Simulation of terahertz plasmons in graphene with grating-gate structures. , 2013, , .		0
190	Effect of self-consistent electric field on characteristics of graphene p-i-n tunneling transit-time diodes. <i>Journal of Applied Physics</i> , 2013, 113, .	2.5	10
191	Voltage-controlled surface plasmon-polaritons in double graphene layer structures. <i>Journal of Applied Physics</i> , 2013, 113, .	2.5	60
192	Terahertz emission and detection using two dimensional plasmons in semiconductor nano-heterostructures for sensing applications. , 2013, , .		0
193	Emission and Detection of Terahertz Radiation Using Two-Dimensional Electrons in III-V Semiconductors and Graphene. <i>IEEE Transactions on Terahertz Science and Technology</i> , 2013, 3, 63-71.	3.1	98
194	Graphene terahertz uncooled bolometers. <i>Journal Physics D: Applied Physics</i> , 2013, 46, 065102.	2.8	38
195	Concept of infrared photodetector based on graphene-graphene nanoribbon structure. <i>Infrared Physics and Technology</i> , 2013, 59, 137-141.	2.9	7
196	Terahertz-Wave Generation Using Graphene: Toward New Types of Terahertz Lasers. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , 2013, 19, 8400209-8400209.	2.9	68
197	Numerical simulation of terahertz plasmons in gated graphene structures. , 2013, , .		2
198	AlGaIn/GaN MIS-gate HEMTs with SiCN gate stacks. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2013, 10, 790-793.	0.8	1

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199	Terahertz photomixing using plasma resonances in double-graphene layer structures. Journal of Applied Physics, 2013, 113, .	2.5	47
200	High-Performance Graphene Field-Effect Transistors With Extremely Small Access Length Using Self-Aligned Source and Drain Technique. Proceedings of the IEEE, 2013, 101, 1603-1608.	21.3	15
201	InGaAs HEMTs with T-gate electrodes formed by multi-layer SiCN molds. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 773-776.	0.8	4
202	Graphene active plasmonic metamaterials for new types of terahertz lasers. , 2013, , .		1
203	Double-graphene-layer terahertz laser: concept, characteristics, and comparison. Optics Express, 2013, 21, 31567.	3.4	34
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